Company Name	Nanjing Huahe Semiconductor Technoligy Co., Ltd	Company Logo
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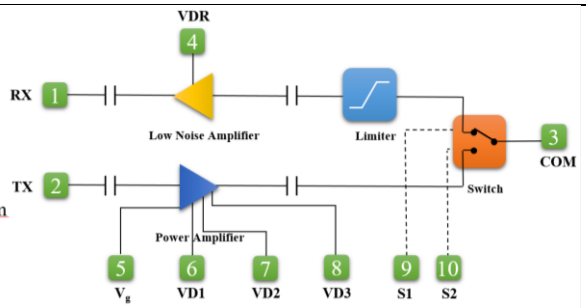
Exhibitor Introduction	Nanjing Huahe Semiconductor Technology Co., Ltd., based in Nanjing, China, is dedicated to the research, development, production, and testing of microwave and millimeter-wave compound monolithic integrated circuits (MMICs). The core technical team comes from leading domestic institutes and has more than 10 years of experience in device design, device modeling, circuit design, chip testing, and packaging. The company provides full supply chain semiconductor services, including IP design, model development and PDK design, wafer-level automated testing, packaging and foundry services, as well as application solution support. With integrated one-stop service, industry-leading cost-effectiveness, fast production capability, and high-quality products, Huahe Semiconductor is committed to meeting the diverse needs of its customers.	
Exhibit Description	Integrated GaAs Transceiver Front-End Chip Series This series of transceiver front-end chips is fabricated using GaAs pHEMT technology, featuring wide bandwidth, high efficiency, and a high level of integration. They are well-suited for phased array T/R modules, satellite communications, and ground-based base stations. The chips adopt a via-through backside metallization process and undergo 100% RF testing to ensure stable and reliable performance. With multi-function integration, the design simplifies transceiver signal chains; dual-supply operation enables both low-noise reception and high-power transmission; and the versatile architecture makes the chips adaptable to a wide range of applications, including counter-UAV systems, satellite links, and communication base stations.	
Exhibit Product	**1. Transceiver front-end chip: HH0812TR-P33-1** 	

Key technical indicators

- Operating frequency: 8 - 12 GHz
- Transmit gain: 23 dB
- Receive gain: 26 dB
- Receive P1dB input power: -18 dBm
- Receive noise figure: 2.8 dB
- Transmit saturated output power: 33 dBm
- Transmit power added efficiency: 38%
- Chip size: 3.0 × 2.7 mm



2. Transceiver front-end chip: HH1418TR-P33-1

Key technical indicators

- Operating frequency: 14 - 18 GHz
- Transmit gain: 20 dB
- Receive gain: 24 dB
- Receive P1dB input power: -19 dBm
- Receive noise figure: 2.9 dB
- Transmit saturated output power: 33 dBm
- Transmit power added efficiency: 30%
- Chip size: 3.0 × 2.7 mm